

Date: - 29 July, 2008

Data Sheet Issue:- 1

Provisional Data

Wespack Rectifier Diode

Types W3864QK100 to W3864QK180

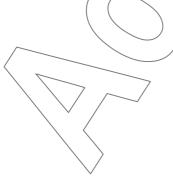
Absolute Maximum Ratings

	VOLTAGE RATINGS) [MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage, (note 1)		1000–1800	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)		1100–1900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{F(AV)M}	Maximum average forward current, T _{sink} =55°C, (note 2)	3864	Α
$I_{F(AV)M}$	Maximum average forward current. T _{sink} =100°C,/(note 2)	2875	Α
I _{F(AV)M}	Maximum average forward current. T _{sink} =100°C, (note 3)	1599	Α
I _{F(RMS)}	Nominal RMS forward current, T _{sink} =25°C _x (note-2)	6965	Α
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 4)	6013	Α
I _{FSM}	Peak non-repetitive surge t _p =10ms, V _m =60%V _{RRM} , (note 5)	22.2	kA
I _{FSM2}	Peak non-repetitive surge t _p ≠10ms, V _{rm} ≤10V, (note 5)	24.4	kA
l ² t	I^2 t capacity for fusing $t_p=10$ ms, $V_m=60\%V_{RRM}$, (note 5)	2.46×10 ⁶	A ² s
l ² t	I ² t capacity for fusing t₀=10ms, V _m ≤10V, (note 5)	2.98×10 ⁶	A ² s
T _{j op}	Operating temperature range	-40 to +180	°C
T _{stg}	Storage temperature range ()	-55 to +180	°C

Notes:-

- 1) De-rating factor of 0.13% per °C is applicable for T_i below 25°C.
- 2) Double side cooled, single phase, 50Hz, 180° half-sinewave.
- 3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, 180°C T_i initial.



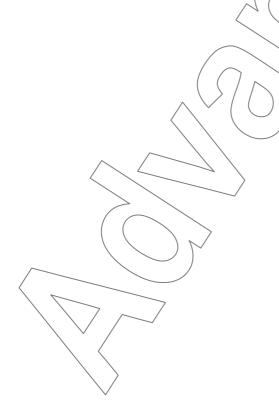


Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	1.20	I _{FM} =3000A	V
V_{FM}	Maximum peak forward voltage	-	-	1.81	I _{FM} =9000A	V
V_{T0}	Threshold voltage	-	-	0.861		V
r _T	Slope resistance	-	-	0.109		mΩ
I _{RRM}	Peak reverse current	-	-	50	Rated V _{RRM}	mA
Q _{rr}	Recovered charge	-	2200	2400		μC
Q _{ra}	Recovered charge, 50% chord	-	1650	- /	I _{τM} =1000A, t _p =1000μs, di/dt=10A/μs,	μC
I _{rm}	Reverse recovery current	-	150	/	V _r =50V	Α
t _{rr}	Reverse recovery time, 50% chord	ı	20	Z - <		μs
		-	-	0.0170	Double side cooled	K/W
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.0303	Anode side cooled	K/W
		-	-	0.0387	Cathode side cooled	K/W
F	Mounting force	16	- /	_20	Note 2	kN
W_t	Weight	-	200	$\overline{}$		g

Notes:-

- 1) Unless otherwise indicated T_i=180°C.
- 2) For other clamp forces, please consult factory.





Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} V	V _{RSM} V	V _R DC
10	1000	1100	7 700
14	1400	1500	930
18	1800	1900	1450

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_i below 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{{V_{T0}}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T} \qquad \text{and:} \qquad W_{AV} = \frac{\Delta T}{R_{th}} \\ \Delta T = T_{j \max} - T_K$$

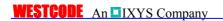
Where V_{T0} =0.861V, r_T =0.109m Ω ,

 $R_{\it th}$ = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance				
Conduction Angle \	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.
Square wave Double Side Cooled	0.0231	0.0207	0.0192	0.0170
Square wave Cathode Side Cooled	0.0417	0.0408	0.0398	0.0387
Sine wave Double Side Cooled	0.0208	0.0181	0.0170	
Sine wave Cathode Side Cooled	0.0404	0.0396	0.0387	

Form Factors				
Conduction Angle 6 phase (60°) 3 phase (120°) ½ wave (180°) d.c.				
Square wave	2.449	1.732	1.414	1
Sine wave	2.778	1.879	1.57	



5.2 Calculating V_F using ABCD Coefficients

The on-state characteristic I_F vs. V_F, on page 6 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F/ii terms of I_F given below:

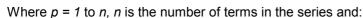
$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		180°C Coefficients	
Α	1.619194	Α	1.310311
В	-0.190117	В	-0.179583
С	-5.461467 × 10 ⁻⁵	/ C_	-4.416532 × 10 ⁻⁵
D	0.023874	Į (0.026656

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$



t = Duration of heating pulse in seconds.

 r_{\downarrow} = Thermal resistance at time t.

 r_p = Amplitude of p_{th} term.

 τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below.



	D.C. Double Side Cooled							
Term	1	2	3	4				
r_p	0.01054152	4.166135×10 ⁻³	9.048202×10 ⁻⁴	1.404721×10 ⁻³				
$ au_{\!p}$	0.2322298	0.05315938	0.0151575	2.630485×10 ⁻³				

	D.C. Cathode Side Cooled					
Term	1	2	3			
r_p	0.02947555	7.046786×10 ⁻³	2.102936×10 ⁻³			
$ au_{p}$	1.276137	0.0795146	3.881676×10 ⁻³			

6.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig. 1

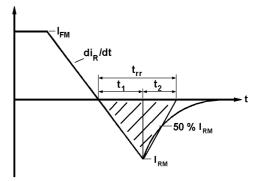
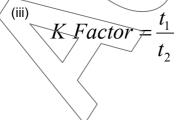
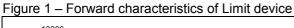


Fig. 1

$$Q_{rr} = \int\limits_{0}^{150 \, \mu s} i_{rr}.dt$$



Curves



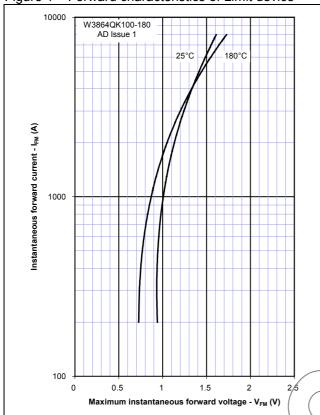
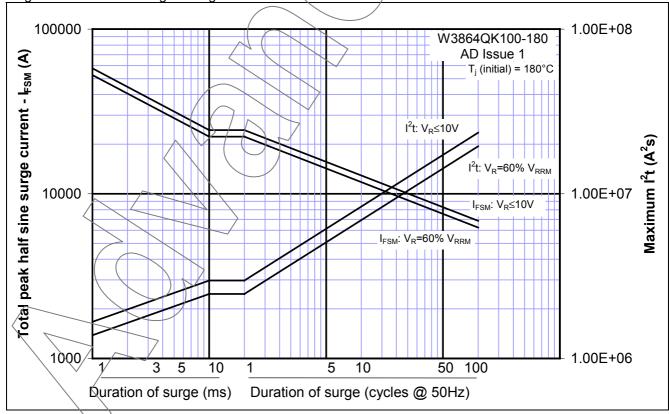
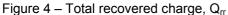


Figure 2 - Transient thermal impedance W3864QK100-180 KSÇ DSC 0.01 Thermal impedance (K/W) 0.001 Q.0001 0.00001 0.000001 1E-05 0.0001 0.001 0.01

Time (s)







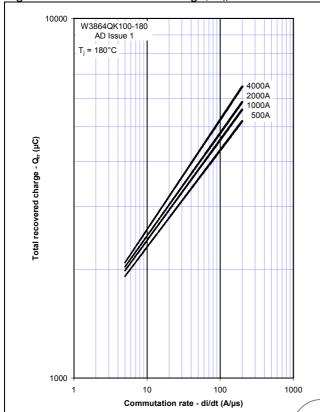
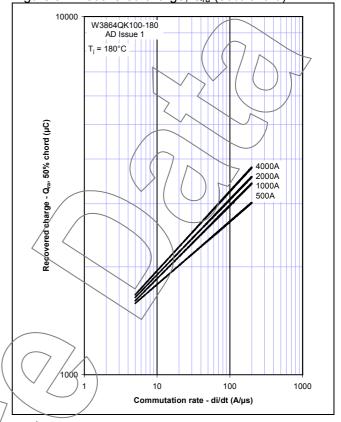


Figure 5 – Recovered charge, Q_{ra} (50% chord)



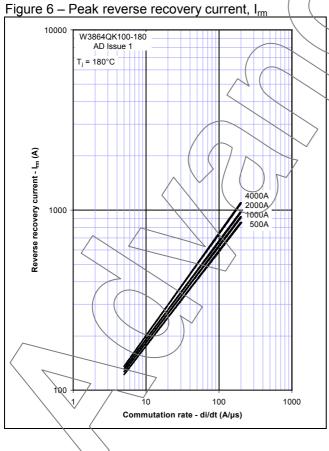


Figure 7 – Maximum recovery time, t_{rr} (50% chord)

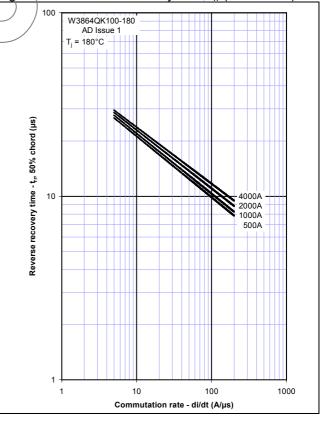


Figure 8 – Forward current vs. Power dissipation – Double Side Cooled

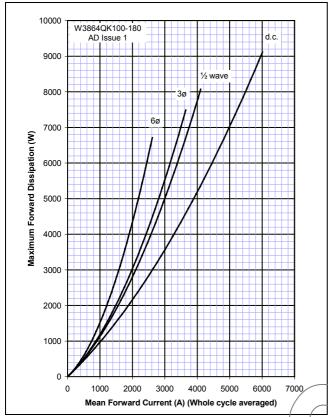


Figure 10 – Forward current vs. Power dissipation – Cathode Side Cooled

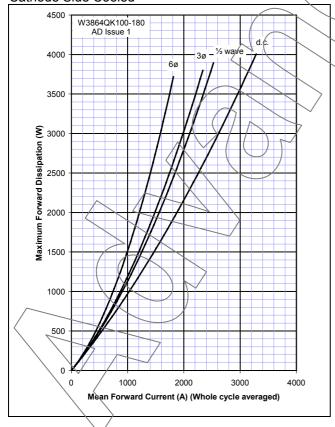


Figure 9 – Forward current vs. Heatsink temperature – Double Side Cooled

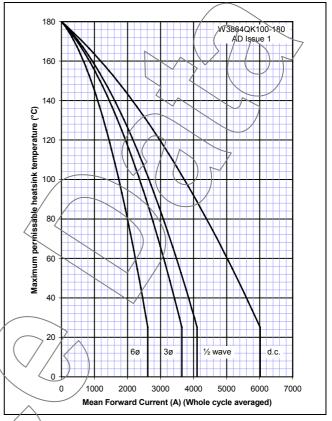
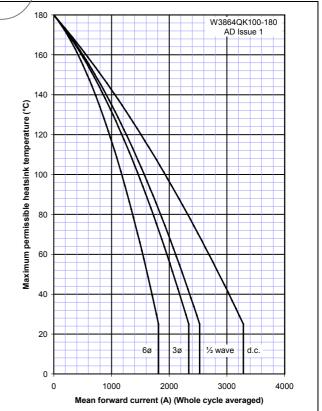
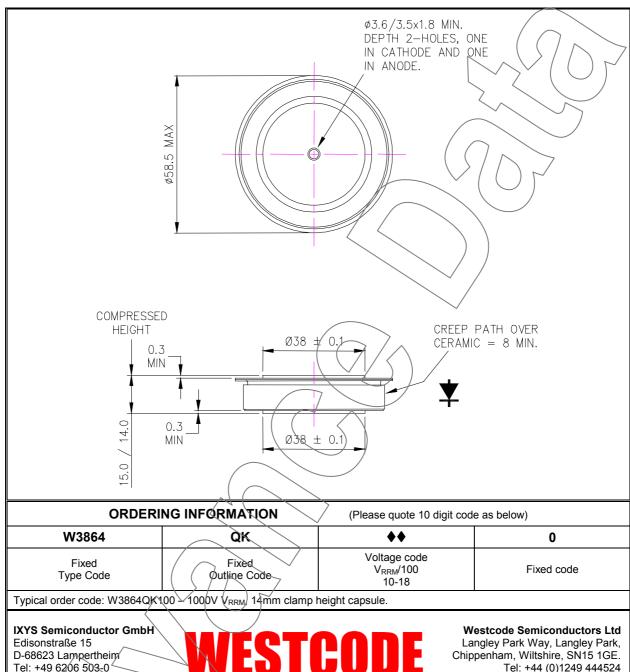


Figure 11 – Forward current vs. Heatsink temperature — Cathode Side Cooled



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